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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/537,804
				Filing Date	June 7, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	1792
				Examiner Name	F.C. Hiteshew
				Attorney Docket Number	204552035400
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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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